- A package consists of two inverse parallel SCR chips
- Welding by vacuum welding technology, which provide high reliability
- Insulated by silicone gel, provide a insulation voltage of 3000V~

- Soft start
- S

All product information are copyrighted and subject to legal disclaimers

(@ T_C = 25℃ unless otherwise specified)

Peak forward voltage	I_T=360A, t_P=380μs	V_T			1.80	V

All product information are copyrighted and subject to legal disclaimers

JMT180KQ16V1C	JMT180KQ16V1C	V1	42.9g/PCS	60 PCS	360 PCS

FIG.1: Forward characteristics(per thyristor)

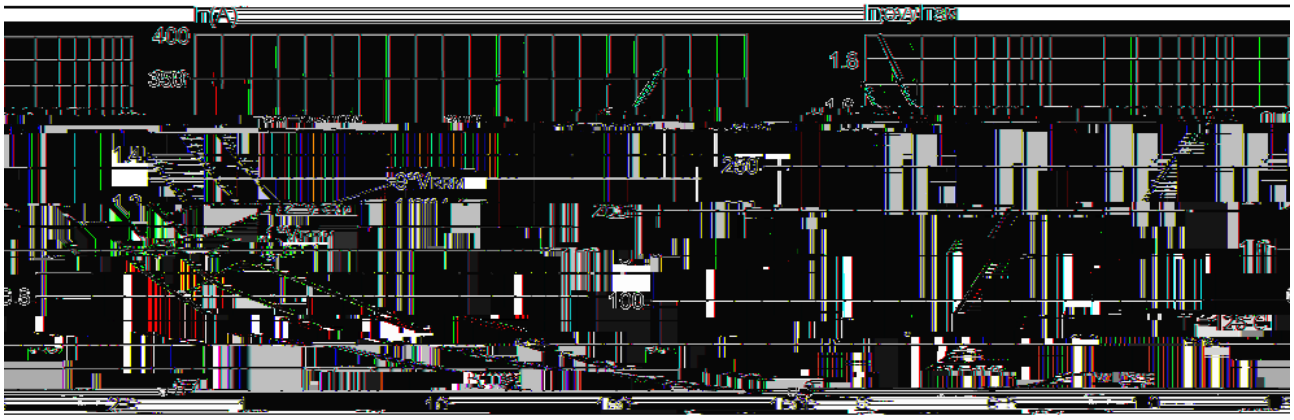


FIG.2: Surge overload current vs. time

FIG.3: Power dissipation per module vs. R.M.S. current

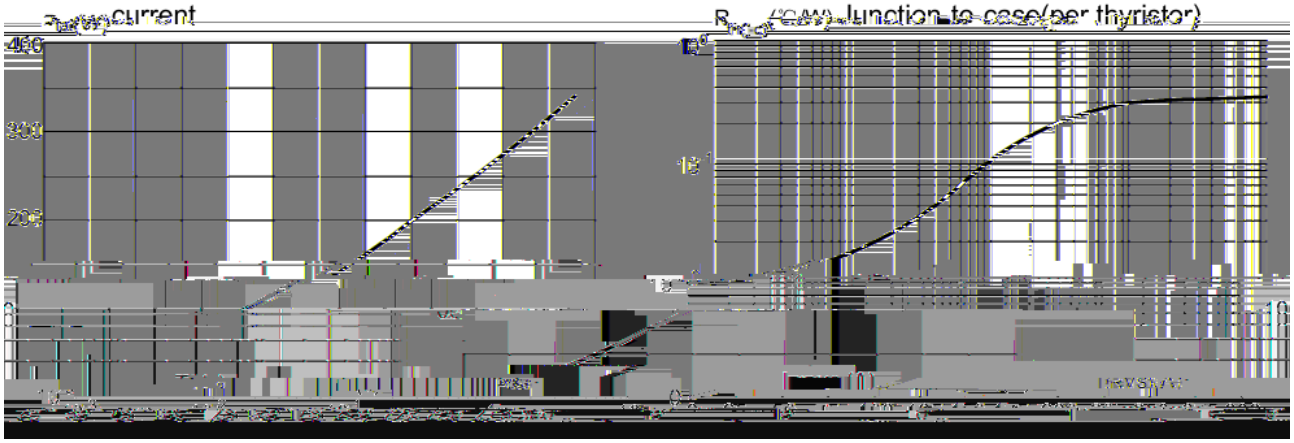
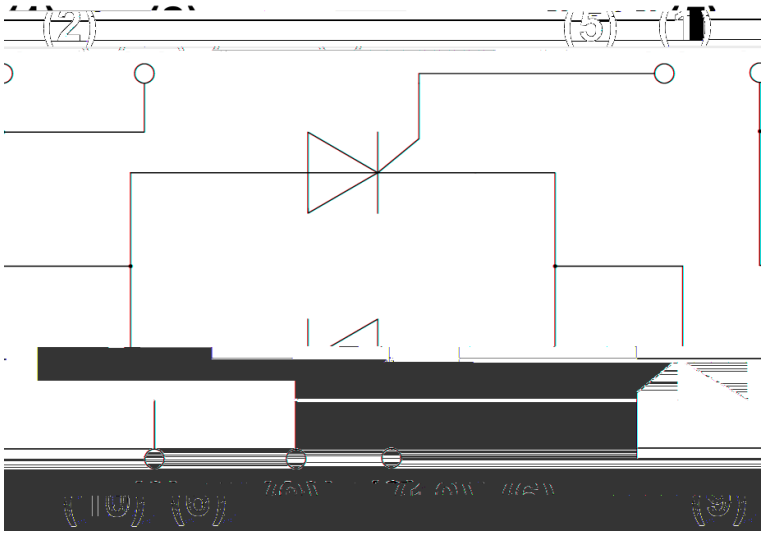
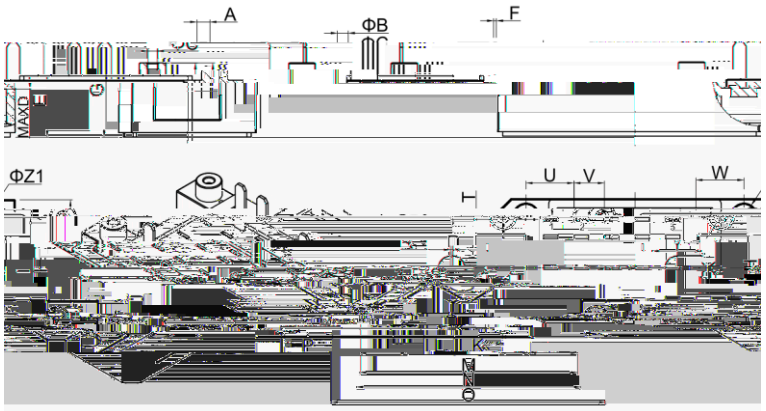


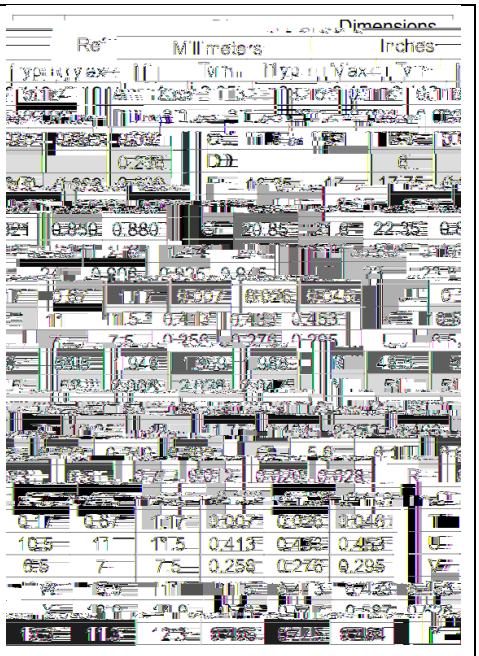
FIG.4: Maximum transient thermal impedance R(°C/W) Junction to case(per thyristor)

All product information are copyrighted and subject to legal disclaimers





Unit of measurement: mm



All product information are copyrighted and subject to legal disclaimers

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Semiconductor Co., Ltd assumes no responsibility for the consequences of use

All product information are copyrighted and subject to legal disclaimers